

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC1626

DESCRIPTION

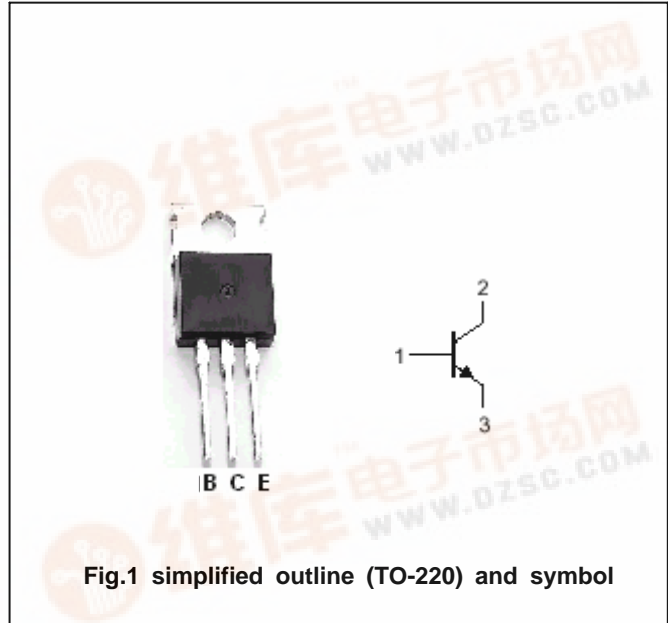
- With TO-220C package
- Complement to type 2SA816

APPLICATIONS

- Designed for the driver stages of 30-50W high-fidelity amplifiers and medium speed switching up to 2A peak current

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	80	V
V _{CEO}	Collector-emitter voltage	Open base	80	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		750	mA
I _{CM}	Collector current-peak		2	A
P _T	Total power dissipation	T _a =25°C	1.5	W
		T _C =25°C	10	
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-50~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	80			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =0.1mA ; I _E =0	80			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =500mA ; I _B =50mA			0.5	V
V _{BE}	Base-emitter on voltage	I _C =500mA ; V _{CE} =2V			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =30V ; I _E =0			0.5	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =5V ; I _C =0			1	μ A
h _{FE-1}	DC current gain	I _C =150mA ; V _{CE} =2V	70		240	
h _{FE-2}	DC current gain	I _C =500mA ; V _{CE} =2V	40			
f _T	Transition frequency	I _C =150mA ; V _{CE} =2V	50			MHz
C _{ob}	Collector output capacitance	I _E =0 ; f=1MHz ; V _{CB} =10V		13		pF

◆ h_{FE-1} Classifications

O	Y
70-140	120-240

